

STGB30V60DF

Trans IGBT Chip N-CH 600V 60A 3-Pin(2+Tab) D2PAK T/R

Manufacturer: STMicroelectronics, Inc

Package/Case: TO-263

Product Type: Thyristors

Lifecycle: Active



Images are for reference only



General Description

This device is an IGBT developed using an advanced proprietary trench gate field stop structure. The device is part of the V series of IGBTs, which represent an optimum compromise between conduction and switching losses to maximize the efficiency of very high frequency converters. Furthermore, a positive VCE(sat)temperature coefficient and very tight parameter distribution result in safer paralleling operation.

Key Features

Maximum junction temperature: TJ= 175 °C

Tail-less switching off

VCE(sat)= 1.85 V (typ.) @ IC= 30 A

Tight parameters distribution

Safe paralleling

Low thermal resistance

Very fast soft recovery antiparallel diode





Recommended For You

STGIF5CH60TS-L

STMicroelectronics, Inc

SDIP2B-26

STGW30NC120HD

STMicroelectronics, Inc

TO-247

STD20NF06LT4

STMicroelectronics, Inc

TO-252

STGW30NC60WD

STMicroelectronics, Inc

TO-247

STGB10NC60HD

STMicroelectronics, Inc

D2PAK

STGIPS10K60A

STMicroelectronics, Inc

SDIP-25L

STGIPS20K60

STMicroelectronics, Inc

SDIP-25

STGW45HF60WD

STMicroelectronics, Inc

TO-247

STGW40H120DF2

STMicroelectronics, Inc

TO-247

STGP30H60DF

STMicroelectronics, Inc

TO-220

STP24NF10

STMicroelectronics, Inc

TO-220

STB75NF75LT4

STMicroelectronics, Inc

TO-263

STGW19NC60HD

STMicroelectronics, Inc

TO-247

STGW40V60DF

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STGW40N120KD

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TO-247